

80V N-ch Power MOSFET

General Features

- Proprietary New Trench Technology
- $R_{DS(ON),typ.}=3.7m\Omega@V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

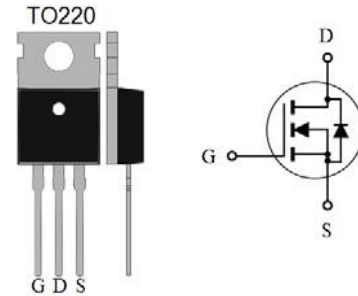
BV_{DSS}	$R_{DS(ON),max.}$	$I_D^{[2]}$
80V	4.7m Ω	179A

Applications

- High efficiency DC/DC Converters
- Synchronous Rectification
- UPS Inverter

Ordering Information

Part Number	Package	Marking
MXP84D7AT	TO-220	MXP84D7AT



Absolute Maximum Ratings

$T_C=25^\circ C$ unless otherwise specified

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	80	V
V_{GSS}	Gate-to-Source Voltage	± 20	
I_D	Continuous Drain Current ^[2]	179	A
	Continuous Drain Current ^[3]	80	
	Continuous Drain Current at $T_C=100^\circ C$ ^[2]	126	
I_{DM}	Pulsed Drain Current at $V_{GS}=10V$ ^[2,4]	716	
E_{AS}	Single Pulse Avalanche Energy ($V_{DD}=50V$, $V_{GS}=10V$, $R_G=25\Omega$, $L=1mH$)	351	mJ
P_D	Power Dissipation	333	W
	Derating Factor above $25^\circ C$	2.22	W/ $^\circ C$
T_L	Soldering Temperature	300	$^\circ C$
	Distance of 1.6mm from case for 10 seconds		
T_J & T_{STG}	Operating and Storage Temperature Range	-55 to 175	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.45	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	

Electrical Characteristics

OFF Characteristics

 $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	80			V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			5	μA	$V_{DS}=80V, V_{GS}=0V$
I_{GSS}	Gate-to-Source Leakage Current			± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$

ON Characteristics

 $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	3.7	4.7	m Ω	$V_{GS}=10V, I_D=80A^{[5]}$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS} = V_{GS}, I_D=250\mu A$
g_{FS}	Forward Transconductance	--	128	--	S	$V_{DS} = 10V, I_D=80A^{[5]}$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance		9.32		nF	$V_{GS}=0V, V_{DS}=25V, f=1.0MHz$
C_{rss}	Reverse Transfer Capacitance		0.26			
C_{oss}	Output Capacitance		0.66			
R_G	Gate Series Resistance		2.85		Ω	$f=1.0MHz$
Q_g	Total Gate Charge		117		nC	$V_{DD}=40V, I_D=80A, V_{GS}=10V$
Q_{gs}	Gate-to-Source Charge		42			
Q_{gd}	Gate-to-Drain (Miller) Charge		31			

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(on)}$	Turn-on Delay Time		52		ns	$V_{DD}=40V, I_D=40A, V_{GS}=10V, R_G=10\Omega$
t_{rise}	Rise Time		135			
$t_{d(off)}$	Turn-off Delay Time		110			
t_{fall}	Fall Time		76			

Source-Drain Body Diode Characteristics

 $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current ^[2]			179	A	Maximum Ratings
I_{SM}	Pulsed Source Current ^[2]			716		
V_{SD}	Diode Forward Voltage		0.85	1.2	V	$I_S=80A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time		83		ns	$V_{GS}=0V, I_F=80A, di/dt=100A/\mu s$
Q_{rr}	Reverse Recovery Charge		206		nC	

Note:

 [1] $T_J = +25^\circ\text{C}$ to $+175^\circ\text{C}$

[2] Silicon limited current only

[3] Package limited current

[4] Repetitive rating, pulse width limited by both maximum junction temperature.

 [5] Pulse width $\leq 380\mu s$; duty cycle $\leq 2\%$.

Typical Characteristics

Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case

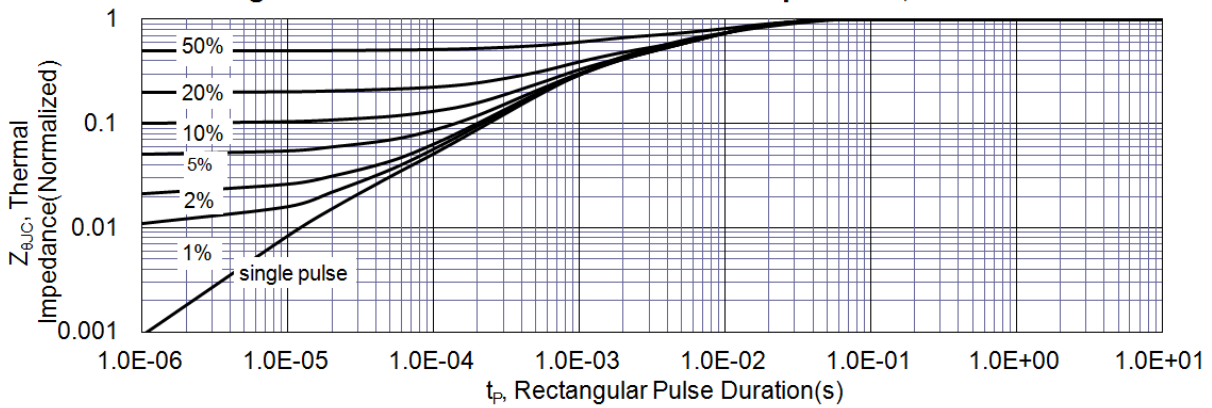


Figure 2. Maximum Power Dissipation vs. Case Temperature

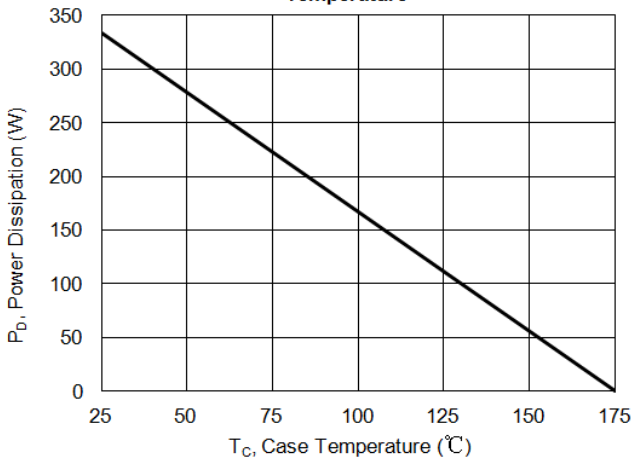


Figure 3. Maximum Continuous Drain Current vs Case Temperature

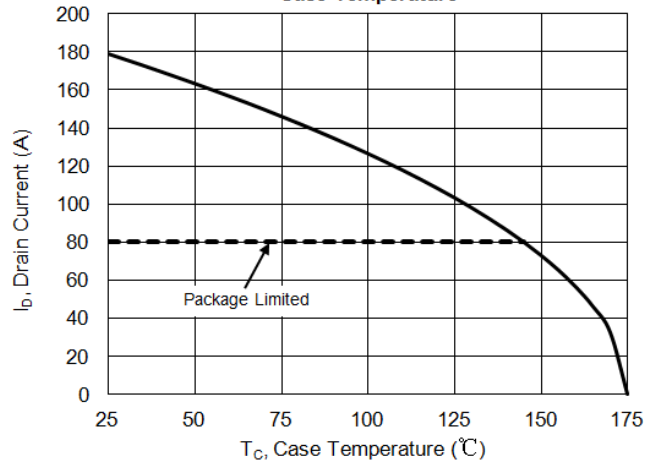


Figure 4. Typical Output Characteristics

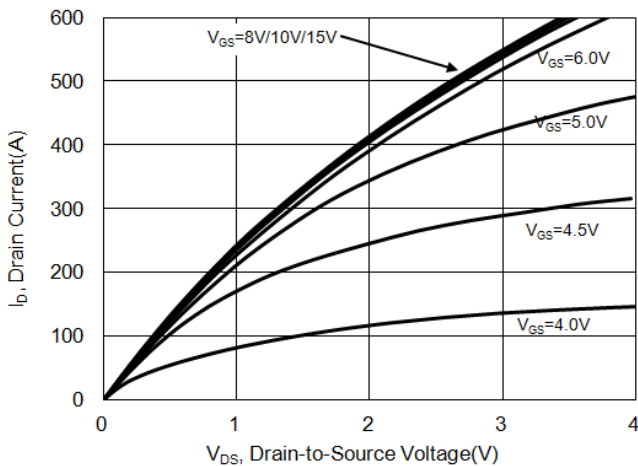


Figure 5. Typical Drain-to-Source ON Resistance vs. Gate Voltage

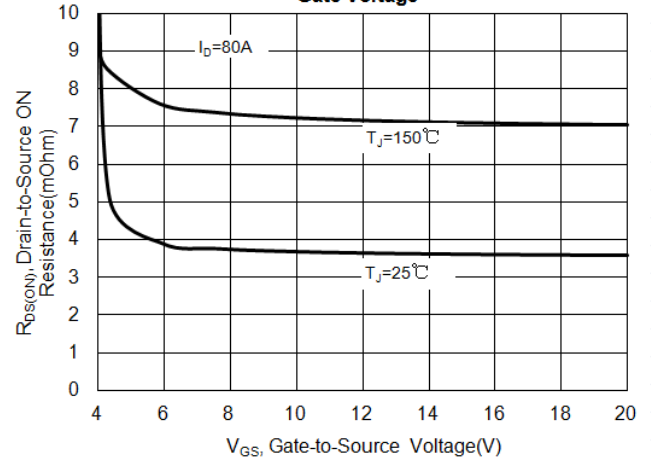


Figure 6. Maximum Peak Current Capability

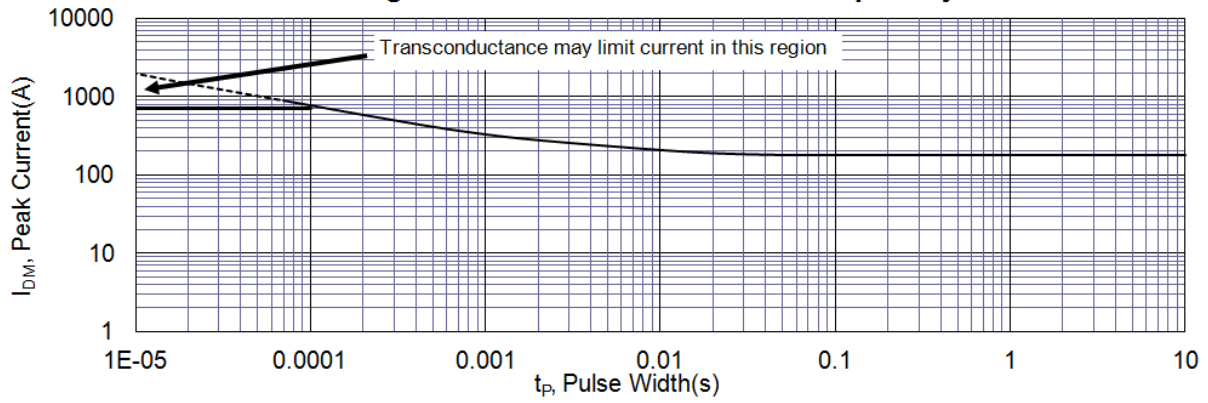


Figure 7. Typical Transfer Characteristics

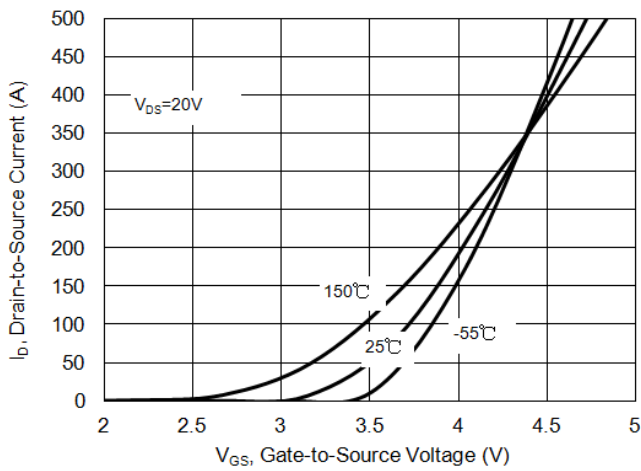


Figure 8. Unclamped Inductive Switching Capability

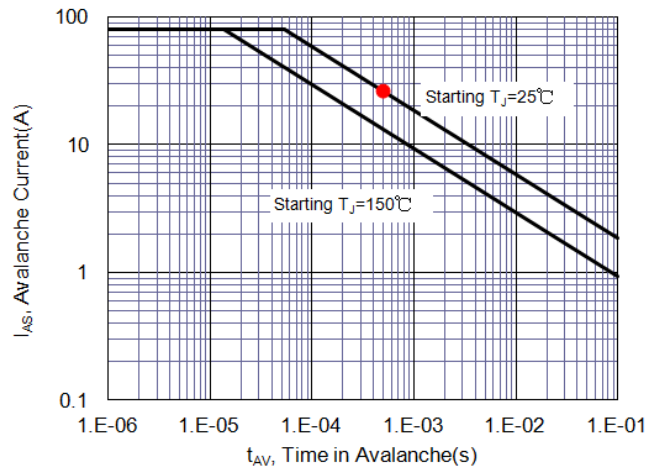


Figure 9. Typical Drain-to-Source ON Resistance

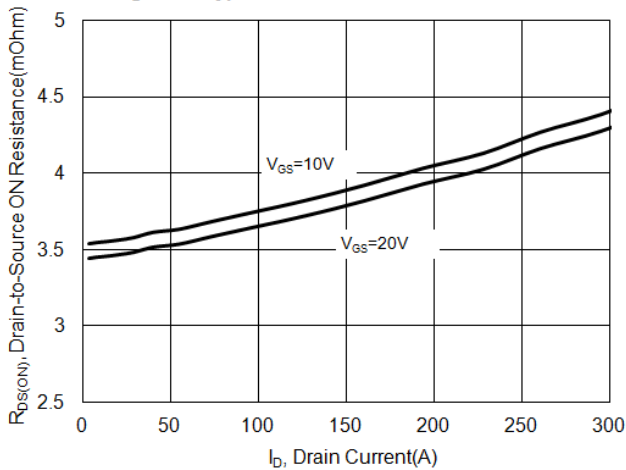


Figure 10. Typical Drain-to-Source On Resistance vs. Junction Temperature

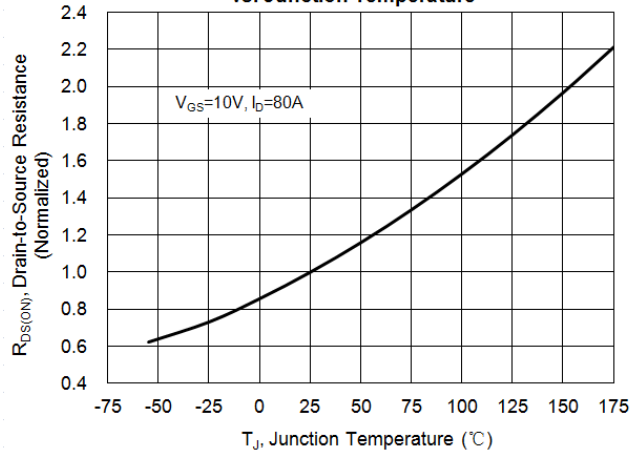


Figure 11. Typical Breakdown Voltage vs. Junction Temperature

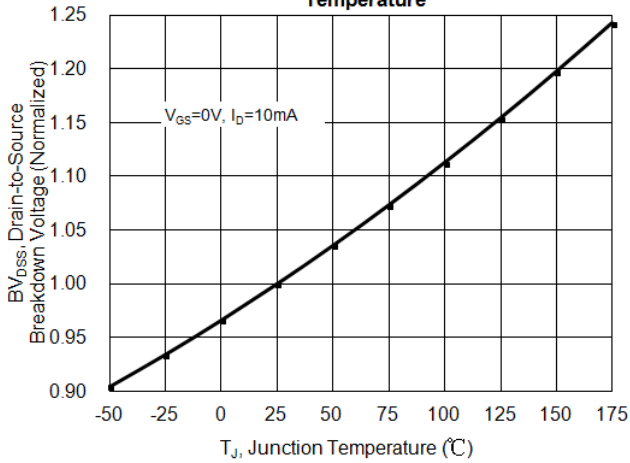


Figure 12. Typical Threshold Voltage vs. Junction Temperature

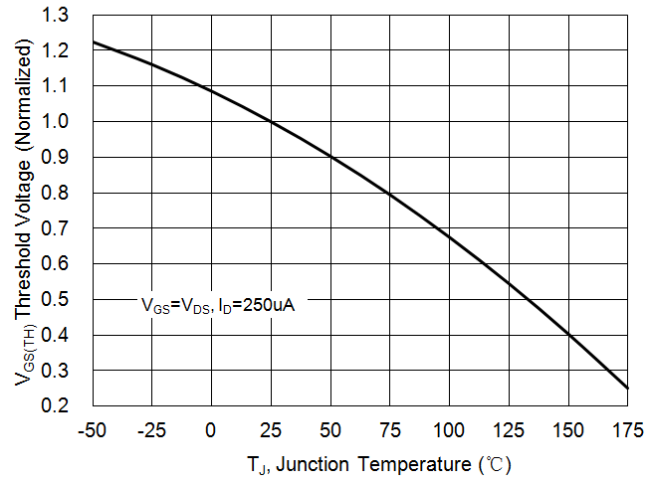


Figure 13. Maximum Forward Safe Operation Area

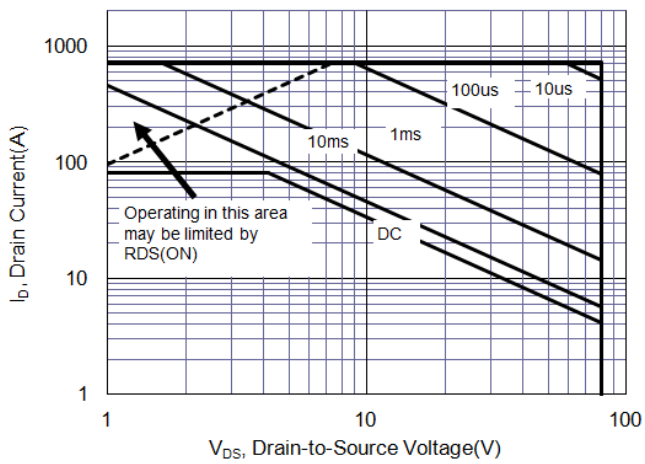


Figure 14. Typical Capacitance vs. Drain-to-Source Voltage

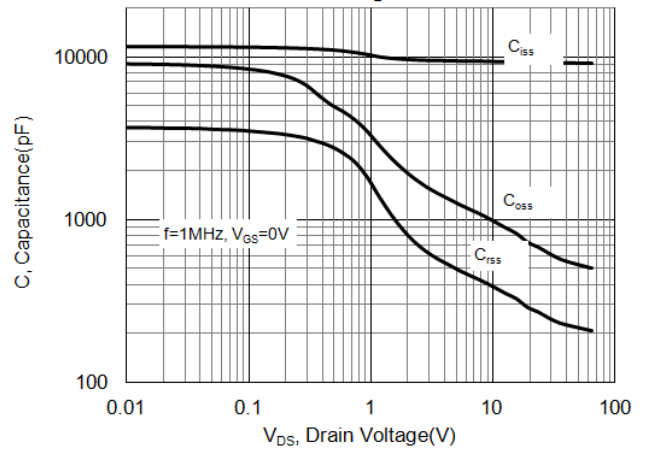


Figure 15. Typical Gate Charge vs. Gate-to-Source Voltage

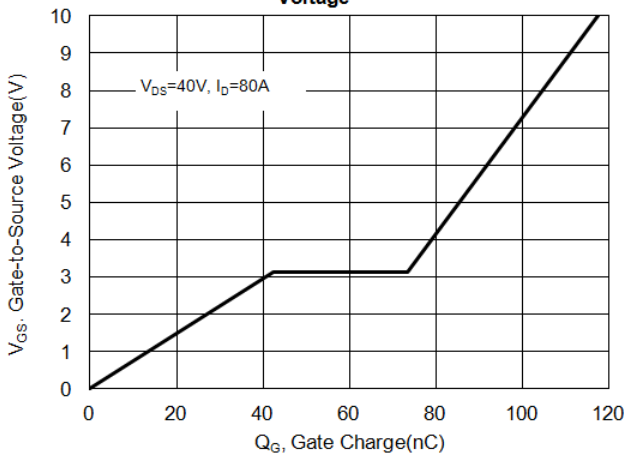


Figure 16. Typical Body Diode Transfer Characteristics

